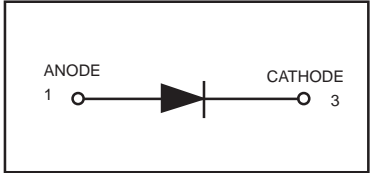
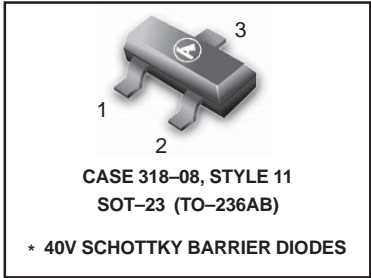


Schottky Barrier Diode

These Schottky barrier diodes are designed for high speed switching applications, circuit protection, and voltage clamping. Extremely low forward voltage reduces conduction loss. Miniature surface mount package is excellent for hand held and portable applications where space is limited.

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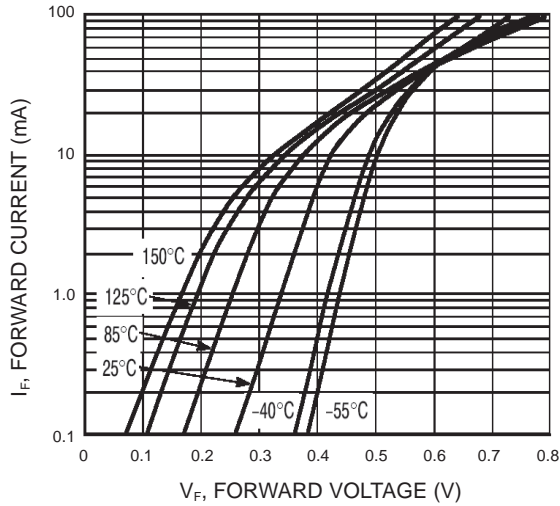
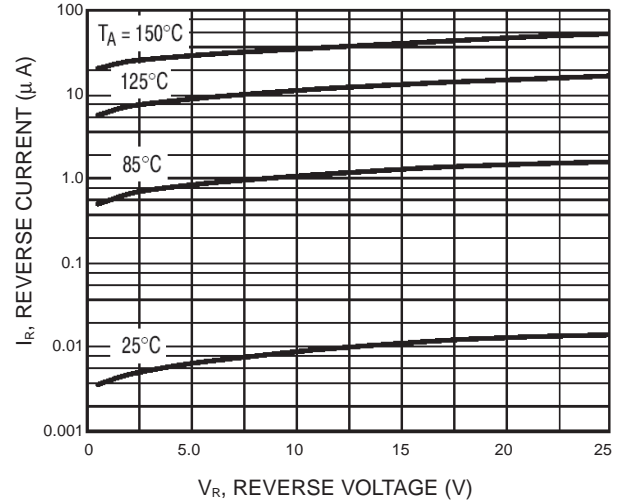
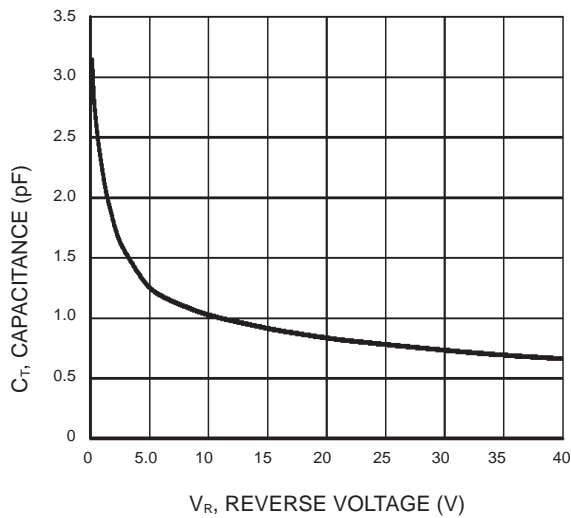


MAXIMUM RATINGS (T_J = 150°C unless otherwise noted)

Rating	Symbol	Value	Unit
Reverse Voltage	V _R	40	Volts
Forward Power Dissipation @ T _A = 25°C	P _F	225	mW
Derate above 25°C		1.8	mW/°C
Operating Junction and Storage Temperature Range	T _J , T _{stg}	-55 to +150	°C

ELECTRICAL CHARACTERISTICS (T_A = 25°C unless otherwise noted)

Characteristic	Symbol	Min	Max	Unit
Reverse Breakdown Voltage (I _R = 10 μA)	V _{(BR)R}	40	—	Volts
Total Capacitance (V _R = 1.0 V, f = 1.0 MHz)	C _T	—	5.0	pF
Reverse Leakage (V _R = 25 V)	I _R	—	1.0	μAdc
Forward Voltage (I _F = 0.1 mAdc)	V _F	—	380	mVdc
Forward Voltage (I _F = 30 mAdc)	V _F	—	500	mVdc
Forward Voltage (I _F = 100 mAdc)	V _F	—	1.0	Vdc

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Figure 1. Typical Forward Current

Figure 2. Reverse Current Versus Reverse Voltage

Figure 3. Typical Current